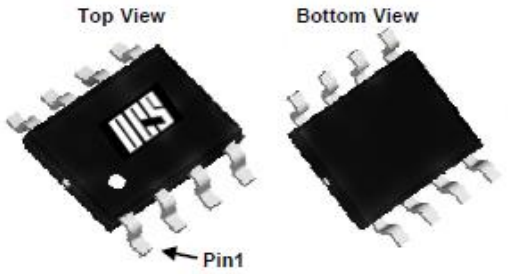
■ General Description

The OCM4614S uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFET may be used to form a level shifted high side switch, and for a host of other applications.



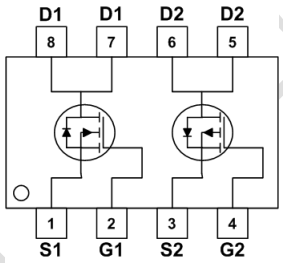
Marking and Pin assignment

■ General Features

N-Channel	P-Channel
V_{DS}= 40V,I_D=7.5A	V_{DS}= -40V,I_D=-7.0A
$R_{DS(ON)}$<27m Ω@ V_{GS}=10V	$R_{DS(ON)}$<32m Ω@ V_{GS}=-10V
$R_{DS(ON)}$<38m Ω@ V_{GS}=4.5V	$R_{DS(ON)}$<46m Ω@ V_{GS}=-4.5V

■ Application

- High power and current handing capability
- BLDC
- Others application



Schematic diagram

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	40	-40	V
Gate-Source Voltage		V_{GS}	±20	±20	V
Continuous Drain Current	T_A=25℃	ID	7.5	-7	A
	T_A=70℃		6	-5.5	
Pulsed Drain Current (Note 2)		I_{DM}	30	-28	A
Single Pulse Avalanche(Note 3)		EAS	16.1	39	mJ
Avalanche Current		I_{AS}	17.8	-27.2	A
Maximum Power Dissipation(Note4)	T_A=25℃	PD	1.5	1.5	W
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55 To 150	-55 To 150	℃

Thermal Characteristic

Parameter	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient(Note 1)	$R_{\theta JA}$	85	℃/W
Thermal Resistance, Junction-to-Case(Note 1)	$R_{\theta JC}$	50	℃/W